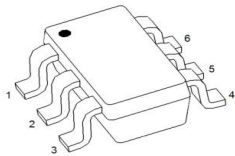
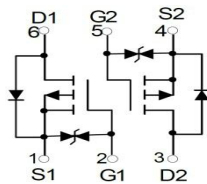


Features

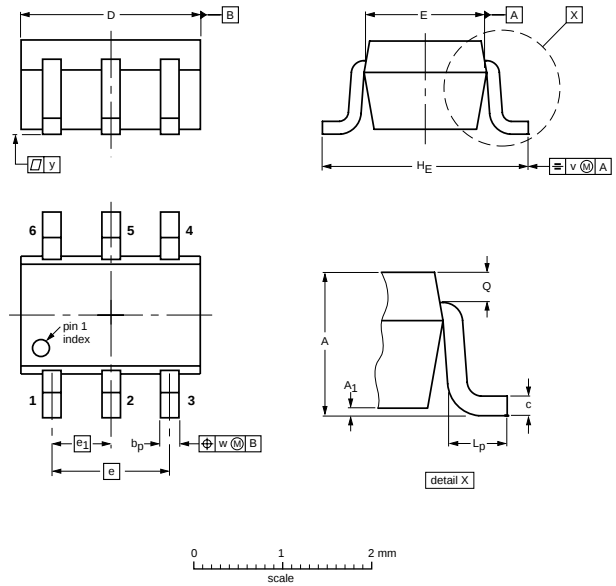
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed



SOT-363



SOT-363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

Maximum Ratings @ T_A = 25 °C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	-50	V
Drain-Gate Voltage (Note 1)	V _{DGR}	-50	V
Gate-Source Voltage	V _{GSS}	20	V
Drain Current (Note 2)	I _D	-130	mA
Total Power Dissipation (Note 2)	P _d	300	mW
Thermal Resistance, Junction to Ambient	R _{JA}	417	C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	C

Note: 1. R_{GS} 20K .

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Electrical Characteristics @ $T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV _{DSS}	-50	-75		V	V _{GS} = 0V, I _D = -250 A
Zero Gate Voltage Drain Current	I _{DSS}			-15 -60	μA μA	V _{DS} = -50V, V _{GS} = 0V, T _J = 25 C V _{DS} = -50V, V _{GS} = 0V, T _J = 125 C
Gate-Body Leakage	I _{GSS}			10	uA	V _{GS} = -20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V _{GS(th)}	-0.8	-1.6	-2.0	V	V _{DS} = V _{GS} , I _D = -1mA
Static Drain-Source On-Resistance	R _{DS (ON)}		6	10		V _{GS} = -5V, I _D = -0.100A
Forward Transconductance	g _{FS}	0.05			S	V _{DS} = -25V, I _D = -0.1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}			45	pF	V _{DS} = -25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{Oss}			25	pF	
Reverse Transfer Capacitance	C _{rss}			12	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}		10		ns	V _{DD} = -30V, I _D = -0.27A, R _{GEN} = 50 Ω , V _{GS} = -10V
Turn-Off Delay Time	t _{D(OFF)}		18		ns	

RATING AND CHARACTERISTIC CURVES (BSS84DW)

